

A Structure, Method and Process for Controlling Band Offset and Alignment at a Crystalline Oxide on Semiconductor Interface

Disclosure Number

200000850

Technology Summary

Structure and Method for Controlling Band Offset and Alignment at a Crystalline Oxide on Semiconductor Interface: Band offset and alignment are manipulated so that COS dielectrics act as an effective dielectric barrier to both electron and hole transport in capacitor and transistor structures.

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